February 2006

FDB8444 N-Channel PowerTrench[®] MOSFET

FAIRCHILD

SEMICONDUCTOR®

FDB8444

N-Channel PowerTrench[®] MOSFET 40V, 70A, 5.5m Ω

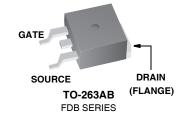
Features

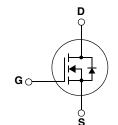
- Typ $r_{DS(on)}$ = 3.9m Ω at V_{GS} = 10V, I_D = 70A
- Typ Q_{g(TOT)} = 91nC at V_{GS} = 10V
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant

Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Transmission
- Distributed Power Architecture and VRMs
- Primary Switch for 12V Systems







Absolute Maximum Ratings T _C = 25°C unless otherwise noted					
Symbol	Parameter	Ratings	Units		
V _{DSS}	Drain to Source Voltage	40	V		
V _{GS}	Gate to Source Voltage	± 20	V		
	Drain Current Continuous (V _{GS} = 10V) (Note	1) 70	Α		
D	Pulsed	Figure 4			
E _{AS}	Single Pulse Avalanche Energy (Note	2) 307	mJ		
	Power Dissipation	167	W		
P _D	Derate above 25°C	1.1	W/ºC		
T _J , T _{STG}	Operating and Storage Temperature	-55 to +175	°C		

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.9	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient TO-263, lin ² copper pad area	43	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB8444	FDB8444	TO-263AB	330mm	24mm	800 units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
B _{VDSS}	Drain to Source Breakdown Voltage	$I_{D} = 250 \mu A, V_{GS} = 0V$	40	-	-	V
		1/ - 221/	-	_	1	Δ

1	Zero Gate Voltage Drain Current	$V_{DS} = 32V$		-	-	1	μA
DSS	Zero Gale Vollage Drain Current	$V_{GS} = 0V$	T _J =150°C	-	-	250	
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20V$		-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	2.6	4	V
		I _D = 70A, V _{GS} = 10V	-	3.9	5.5	
r _{DS(on)}	Drain to Source On Resistance	$I_D = 70A, V_{GS} = 10V, T_J = 175^{\circ}C$	-	7	9.9	mΩ

Dynamic Characteristics

Ciss	Input Capacitance			-	6040	8035	рF
Coss	Output Capacitance		V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		480	640	pF
C _{rss}	Reverse Transfer Capacitance				290	435	pF
R _G	Gate Resistance	f = 1MHz	f = 1MHz		2	-	Ω
Q _{g(TOT)}	Total Gate Charge at 10V	V _{GS} = 0 to 10V		-	91	128	nC
Q _{g(TH)}	Threshold Gate Charge	$V_{GS} = 0$ to 2V	V _{DD} =20V,	-	7	10	nC
Q _{gs}	Gate to Source Gate Charge		I _D = 70A,	-	23	-	nC
Q _{gs2}	Gate Charge Threshold to Plateau			-	17	-	nC
Q _{gd}	Gate to Drain "Miller" Charge			-	20	-	nC

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Switching	g Characteristics					
t _(on)	Turn-On Time		-	-	135	ns
t _{d(on)}	Turn-On Delay Time		-	12	-	ns
t _r	Turn-On Rise Time	$V_{DD} = 20V, I_D = 70A$ $V_{GS} = 10V, R_{GS} = 2\Omega$	-	78	-	ns
t _{d(off)}	Turn-Off Delay Time		-	48	-	ns
t _f	Turn-Off Fall Time		-	15	-	ns
t _{off}	Turn-Off Time		-	-	95	ns
Drain-So	urce Diode Characteristics			1	I	
V _{SD}	Source to Drain Diode Voltage	I _{SD} = 70A	-	-	1.25	V
Source to Drain Didde Voltage	Source to Brain Blode Voltage	I _{SD} = 35A	-	-	1.0	V

I_F = 70A, di/dt = 100A/μs

I_F = 70A, di/dt = 100A/μs

t_{rr} Q_{rr}

Reverse Recovery Time

Reverse Recovery Charge

Notes: 1: Maximum wire current carrying capacity is 70A. 2: Starting $T_J = 25^{\circ}C$, L = 0.2mH, $I_{AS} = 56A$.

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: http://www.aecouncil.com/ All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

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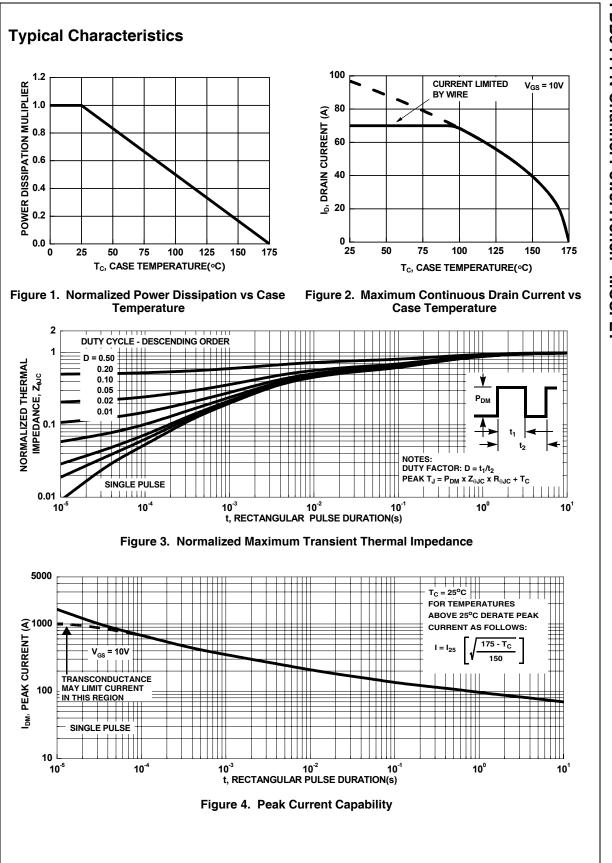
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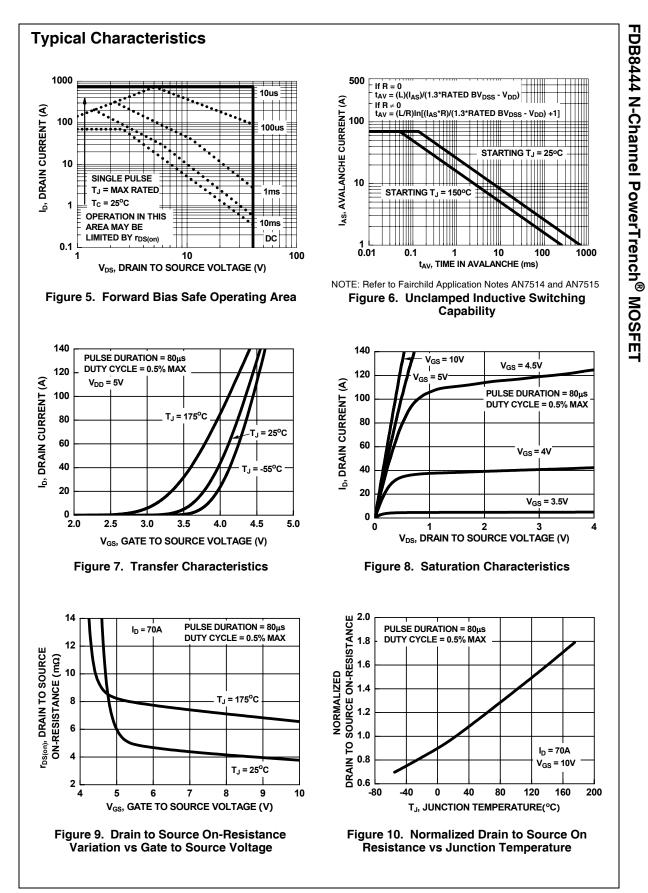
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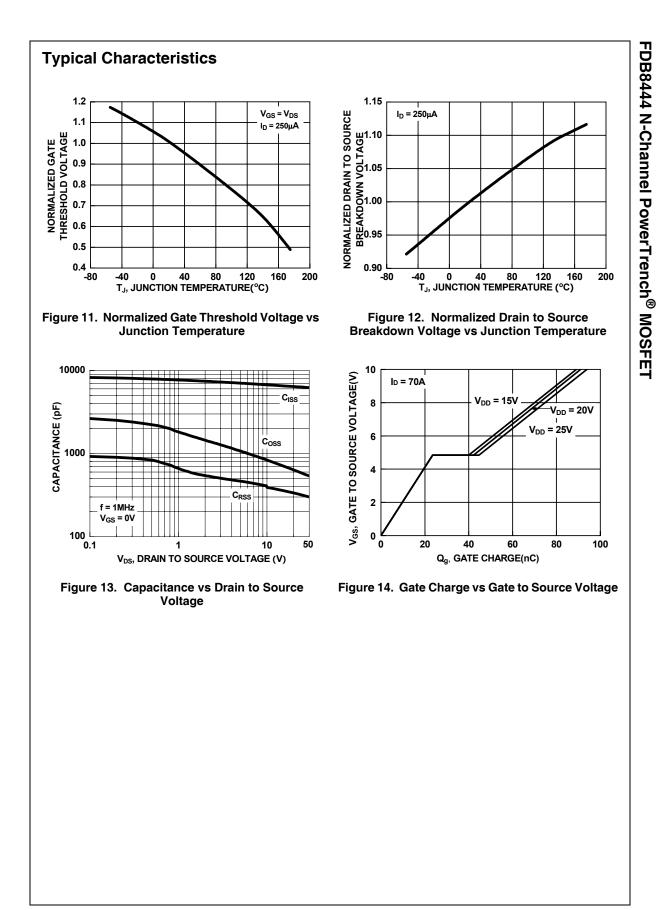
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